

GP1S194HCZ0F

Gap: 1.7mm, Slit: 0.3mm Phototransistor Output, **Compact Transmissive Photointerrupter**



■Description

GP1S194HCZ0F is a compact and low-profile, transmissive photointerrupter with photo-transistor output and detects an object between the emitter and the detector.

The compact package has been molded by a unique technology that is a combination of transfer and injection molding.

■Features

1. Transmissive with phototransistor output

2. Compact Gap Width: 1.7mm 3. Slit Width (detector side): 0.3mm 4. Package: 3.6×2.0×2.7mm

5. RoHS directive compliant

1. Compliant with RoHS directive (2002/95/EC)

■Agency approvals/Compliance

■Applications

1. General purpose detection of object presence or motion.

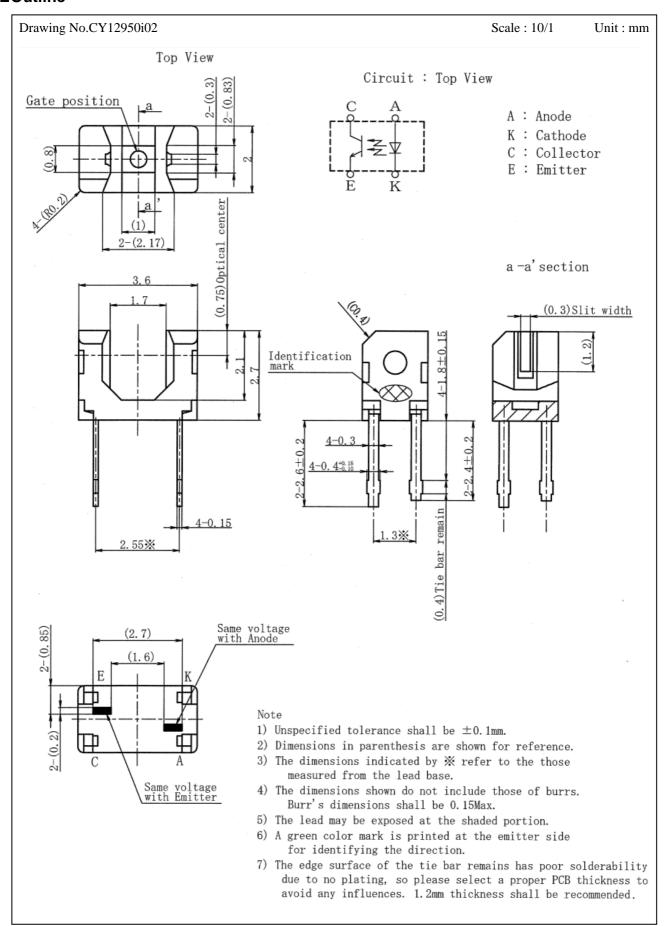
Example: Printer, lens control for camera

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Sheet No.: OP13028EN



■Outline



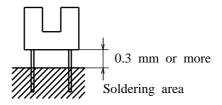


■Absolute maximum ratings

Ta=25°C

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_{F}	30	mA
	Reverse voltage	V_R	6	V
	Power dissipation	P	75	mW
	Collector-emitter voltage	V_{CEO}	35	V
Output	Emitter-collector voltage	V_{ECO}	6	V
	Collector current	Ic	20	mA
	Collector power dissipation	Pc	75	mW
	Total power dissipation	Ptot	100	mW
	Operating temperature	Topr	-25 to +85	°C
Storage temperature * Soldering temperature		Tstg	-40 to +100	°C
		Tsol	260	°C

^{*} Soldering time : 3 s or less

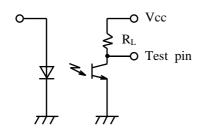


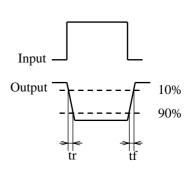
■Electro-optical characteristics

Ta=25°C

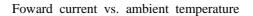
Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
T	Forward voltage		V_{F}	I _F =20mA	-	1.2	1.4	V
Input	Reverse current		I_R	V _R =3V	-	-	10	μΑ
Output	Collector dark current		I_{CEO}	V _{CE} =20V	-	-	100	nA
Transfer characteris tics	Collector current		Ic	V _{CE} =5V, I _F =5mA	150	-	600	μΑ
	Response time	(Rise)	tr	V _{CE} =5V, Ic=100μA	-	50	150	μs
		(Fall)	tf	$R_L=1k\Omega$	-	50	150	μs
	Collector-emitter saturation voltage		V _{CE} (sat)	I _F =10mA, Ic=40μA	-	-	0.4	V

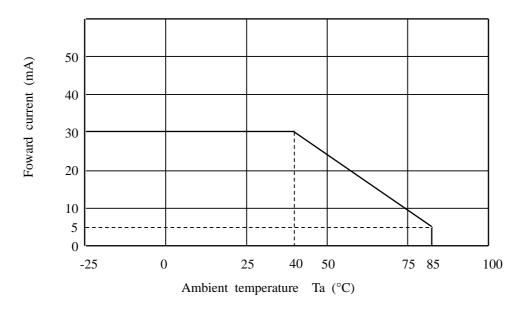
(Test circuit for response time)

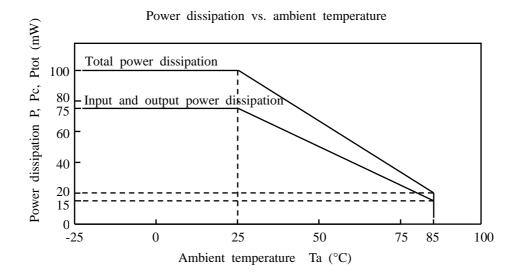






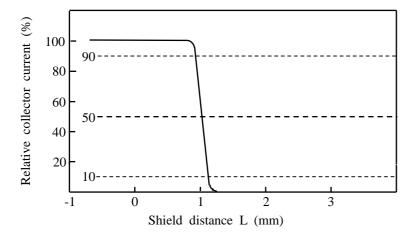


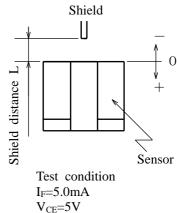






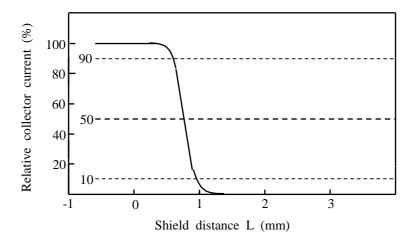
Relative collector current vs. shield distance 1 (Reference value)

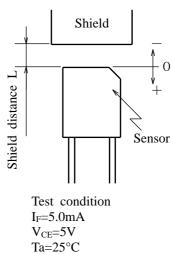




Ta=25°C

Relative collector current vs. shield distance 2 (Reference value)







■Supplements

Parts

Refer to the attached sheet, Page 8.

Packing

Refer to the attached drawing No. CY12951i09B, Page 9.

•ODS materials

This product shall not contain the following materials.

Also, the following materials shall not be used in the production process for this product.

Materials for ODS: CFC_S, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methyl chloroform)

• Specified brominated flame retardants

Specified brominated flame retardants (PBB and PBDE) are not used in this device at all.

- •Compliance with each regulation
 - 1) The RoHS directive(2002/95/EC)

This product complies with the RoHS directive(2002/95/EC)

Object substances: mercury,lead, cadmium,hexavalent chromium,polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE)

2) Content of six substances specified in Management Method for Control of Pollution Caused by Electronic

Information Products Regulation (Chinese : 电子信息产品污染控制管理办法).

	Toxic and hazardous substances					
Category	Lead (Pb)	Mercury (Hg)	Cadmium (Cd)	Hexavalent chromium (Cr ⁶⁺)	Polybrominated biphenyls (PBB)	Polybrominated diphenyl ethers (PBDE)
Photointerrupter	✓	1	1	✓	✓	✓

^{✓:} indicates that the content of the toxic and hazardous substance in all the homogeneous materials of the part is below the concentration limit requirement as described in SJ/T 11363-2006 standard.

•Product mass : Approximately 24mg

•Country of origin: Japan and China



■Notes

•Circuit design

In circuit designing, make allowance for the degradation of the light emitting diode output that results from long continuous operation. (50% degradation/5 years)

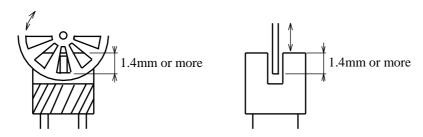
Prevention of detection error

To prevent photointerrupter from faulty operation caused by external light, do not set the detecting face to the external light.

•Position of opaque board

Opaque board shall be installed at place 1.4mm or more from the top of elements.

(Example)



Soldering

To solder onto lead pins, solder at the position of 0.3mm or more from the package's bottom at 260°C for 3s or less. Please don't bend lead pins from the root of package when soldering.

Please also take care not to let any external force exert on lead pins.

Please don't do soldering with preheating, and please don't do soldering by reflow.

Please have soldering adjustment, etc. after GP1S194HCZ0F is cooled down, and also note that the outer mold resin may be meltdown by heating for a long time.

Cleaning

Cleaning shall be carried out under the below conditions to avoid keeping solvent, solder and flux on the device.

- (1) Solvent cleaning: Solvent temperature 45°C or less, Immersion for 3min. or less
- (2) Ultrasonic cleaning: Since the influence to the product may changes by the conditions of the ultrasonic power, time, the tank size, PCB size, the product installation condition, etc., please evaluate with actual conditions and confirm before usage.
- (3) The cleaning shall be carried out with solvent below. Solvent: Ethyl alcohol, Methyl alcohol

•Lead pin

Lead terminals of this product are tin copper alloy plated. Before usage, please evaluate solder ability with actual conditions and confirm. The uniformity in color for the lead terminals are not specified.



■Parts

This product uses the below parts.

•Light detector (Quantity: 1)

Type Material		Maximum sensitivity (nm)	Sensitivity (nm)	Response time (µs)
Phototransistor	Silicon (Si)	930	700 to 1200	20

•Light emitter (Quantity: 1)

Туре	Material	Maximum light emitting wavelength (nm)	I/O Frequency (MHz)
Infrared light emitting diode (non-coherent)	GaAs	950	0.3

Material

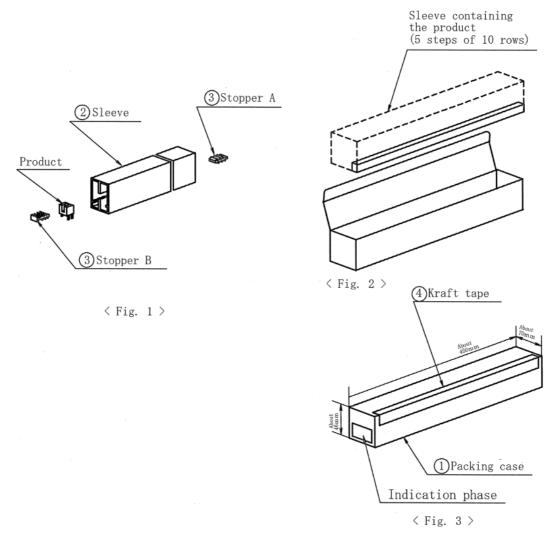
Case	Lead frame	Lead frame plating	
Black PPS resin (UL 94V-0)	42 Alloy	SnCu plating	

•Others

This product shall not be proof against radiation flux.



■Packing (Drawing No.:CY12951i09B)



1. Packing material

Νο	Name	material	The number of use
1	Packing case	Paper corrugated cardboard	1
2	Sleeve	Polycarbonate	50
3	Stopper A, B	rubber	50, respectively
4	Kraft tape		

2. Packing quantity

- 1. Packing sleeve: 200pieces per 1 sleeve
- 2. Packing case: 10000pieces per 1 case

(Gross weight: Approx 850 g)

3. Indication items

The contents of the carton indication conforms to EIAJ C-3 and the following items are indicated.

Model No., Internal production control name, Quantity, Packing date, Corporate name, Country of origin

4. Packing method

- 1. 200 products are contained to a sleeve. (The receipt method is shown in the above figure.) <Fig. 1>
- 2. 50 sleeves (5 steps of 10 rows) are contained into a packing case. ${\rm <Fig.\,2>}$
- 3. The packing case is sealed off with the kraft tape. Indicates on the packing case Model No., Internal production control name, Quantity, Packing date, Corporate name, Country of origin. <Fig. 3>